

Title (en)

FABRICATION METHOD OF A NANODEVICE STRUCTURE

Title (de)

HERSTELLUNGSVERFAHREN FÜR EINE NANOVORRICHTUNGSSTRUKTUR

Title (fr)

PROCÉDÉ DE FABRICATION D'UNE STRUCTURE DE NANODISPOSITIF

Publication

EP 2038208 A1 20090325 (EN)

Application

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Priority

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Abstract (en)

[origin: WO2008004777A1] A nanodevice structure according to the present invention includes a substrate (10) having alignment marks (16) formed thereon, a plurality of nanomaterial layers (20) applied on the substrate, and electrodes formed to be in partial contact with the upper surface of the nanomaterial layer (20) in order to obtain easy application of the nanomaterial layer (20) and low contact resistance between the electrodes and the nanomaterial layer (20).

IPC 8 full level

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